# Model SE103 Pressure Sensor Dies



Made from high quality silicon wafer of 4" diameter, BCM SE103 sensor dies are in mass production by means of Micro-Electro-Mechanical System (MEMS) technology. Based on piezoresistive effect, BCM SE103 pressure sensor dies can measure the pressure concerned on its surface. The back side of a SE103 die is a pressure chamber, it can be sealed with glass to measure sealed gauge pressure or absolute pressure. If the sealed glass is with a vent, the dies are used to measure gauge or differential pressure.

The pressure ranges of SE103 are from 0~200 mbarG up to 0~1000 barA, in the form of gauge(or differential (diff.)) pressure or absolute pressure. The measuring accuracy is up to 0.25% fso (fso = full scale output). The output signal is Wheatstone bridge output in millivolt. For bridge excitation, constant current (1 mA) or constant voltage (5~10 Vdc) excitation method is available on request.



SE103 pressure sensing element wafer

#### Wheatstone bridge circuit:



#### sketch of the cross-section of SE103:



### terminal pads layout:



2.70 x 3.45 (for maximum pressure ≤ 25 bar)



2.45 x 2.45 (for maximum pressure  $\geq$  40 bar)

## BCM SENSOR TECHNOLOGIES BVBA

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## Model SE103 Pressure Sensor Dies



### **Specifications:**

parameters		units	specifications
pressure ranges*	gauge pressure	barG	0/0.2, /0.35, 0/1, /2.5, /4, /6, /10, /16, /25
	absolute pressure	barA	0/1, /2.5, /4, /6, /10, /16, /25, /40, /60, /100, /250, /400, /600, /1000
overload pressure		%fs	200 (≤ 100 bar), 150 ( > 100 bar), not over 1000 bar
full scale output		mV	35 ± 5 ( ≤ 0.35 bar), 80 ± 20 ( > 0.35 bar)
excitation	current (recommended)	mA	0.5,, 1.5
	voltage	Vdc	5,, 10
ZERO offset		mV	≤ ± 40
non-linearity (NL)		%fso	± 0.25 (typical), ± 0.5, ± 1
hysteresis (HY)		%fso	≤ ± 0.1
repeatability (RP)		%fso	≤ ± 0.2
long term stability		%fso/year	≤ ± 0.2
short term stability		%fso/8 hours	≤ ± 0.1
bridge resistance		kΩ	5 ± 1
storage temperature		°C	-45 ~ +125
operating temperature		°C	-45 ~ +100
TC of bridge resistance		10 <sup>-3</sup> /°C	1.15 ± 0.25
TC of sensitivity		%fso/°C	< ± 0.1
TC of offset		%fso/°C	< ± 0.1
thermal hysteresis of offset		%fso/°C	< ± 0.02
PN junction break down voltage		V (@ 10 µA)	≥ 20
dimensions		mm	2.70 x 3.45 x 0.4 (≤ 25 bar),2.45 x 2.45 x 0.4 (≥ 40 bar)

The listed specifications and dimensions are subject to change without prior notice.

Conditions: excitation = 1 mA, T = 25 °C, NL is calculated using the "least square method".

\*: Please refer to the ordering code for the available pressure ranges.

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#### Ordering Code Explanation: SE103 - 60 - A - II - c - a - G8

Model SE103 silicon pressure sensor die, for absolute pressure measurement of 0~60 bar. The NL of this die is 0.5% fs. The bridge will be excited by constant current. The die dimensions are 2.45 mm x 2.45 mm x 0.4 mm and the die is finished with glass base of 0.8 mm thickness.



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